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**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of: **Labelle, et al.**

Serial No.: **10/705,347**

Filed: **November 8, 2003**

For: **Method for Integrating a High-K Gate  
Dielectric in a Transistor Fabrication  
Process**

Art Unit: Unknown

Examiner: Unknown

**INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir or Madam:

In this Information Disclosure Statement and pursuant to 37 C.F.R. §§ 1.56 and 1.97, Applicants hereby disclose to the Patent Office patents, publications or other information of which Applicants are aware. A copy of a Form 1449 identifying the patents and other materials is submitted herewith.

The items identified in this Information Disclosure Statement may or may not be “material” as defined in 37 C.F.R. § 1.56, and the submission thereof by Applicants is not to be construed as an admission that any such patent, publication or other information referred to is material or considered to be material (37 C.F.R. § 1.97(h)), or even qualifies as “prior art” under 35 U.S.C. § 102 with respect to the present invention unless specifically designated by Applicants as such. Identification of any reference or patent herein is not an admission, nor is it to be construed as an admission, that it was invented prior to the invention disclosed herein.

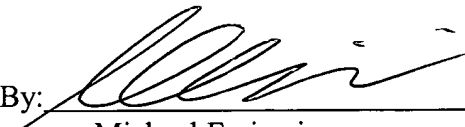
The filing of this Information Disclosure Statement is not to be construed to mean that a search has been made or that no other material information, as defined in 37 C.F.R. § 1.56, exists.

In accordance with 37 C.F.R. § 1.97(b), no fee is believed due at this time since the Information Disclosure Statement is being filed before the mailing date of the first Office action on the merits. Also, in accordance with 37 C.F.R. § 1.97(e)(1), each item of information contained in this Information Disclosure Statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Information Disclosure Statement.

The Assistant Commissioner is hereby authorized to charge or credit Deposit Account Number 50-0731 for any deficiency or overpayment in the fees required for the filing of this Information Disclosure Statement, for which purpose a duplicate copy of this paper is also included.

Respectfully submitted,  
Farjami & Farjami LLP

Dated: 3/15/05

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CERTIFICATE OF MAILING

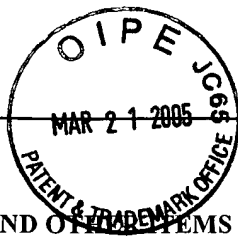
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<b>FORM PTO-1449</b>  <b>LIST OF PATENTS AND OTHER DOCUMENTS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>  (Use several sheets if necessary)	<b>ATTY. DOCKET NO.</b> 0180151	<b>SERIAL NO.</b> 10/705,347
	<b>APPLICANTS:</b> Labelle, et al.	
	<b>FILING DATE:</b> November 8, 2003	<b>GROUP ART:</b> Unknown

U.S. PATENT DOCUMENTS							
Exam. Initials		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
	1	2003/0218223 A1	11/27/2003	Nishiyama, et al.			
	2	2003/0119334 A1	6/26/2003	Kwak, et al.			
	3	5,344,522	9/6/1994	Yagi, et al.			
	4	6,159,849	12/12/2000	Kang, et al.			

FOREIGN PATENT DOCUMENTS								
Exam. Initials		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUB CLASS	TRANSLATION	
							YES	NO
	1	JP 2003/249649 A	9/5/2003	Japan				
	2	JP 2003/008005 A	1/10/2003	Japan				
	3	JP 06350093 A	12/22/1994	Japan				
	4	JP 08316466 A	11/29/1996	Japan				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)		
	1	Cho et al, <i>Novel Nitrogen Profile Engineering for Improved TaN/HfO<sub>2</sub>/Si MOSFET Performance</i> , IEEE, 655-658 (December, 2001)
	2	Choi et al, <i>High-Quality Ultra-thin HfO<sub>2</sub> Gate Dielectric MOSFETs with TaN Electrode and Nitridation Surface Preparation</i> , Digest of Technical Papers, JSAP, 15-16 (2001)

<b>EXAMINER:</b>	<b>DATE CONSIDERED:</b>
<b>EXAMINER:</b> Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include a copy of this form with next communication to applicant. <b>Information Disclosure Statement-- Section 9 PTO-1449</b>	